

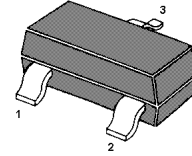
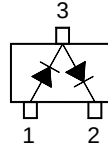
SB706D-40

SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

For low current rectification

Features

- High reliability
- Low reverse current



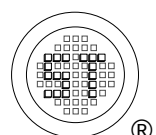
Marking Code: "ZE"
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Average Rectified Forward Current	I_O	30	mA
Peak Forward Surge Current ($t = 8.3$ ms)	I_{FSM}	200	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage at $I_F = 1$ mA	V_F	-	-	0.37	V
Reverse Current at $V_R = 10$ V	I_R	-	-	1	μA
Reverse Breakdown Voltage at $I_R = 10$ μA	$V_{(BR)R}$	45	-	-	V
Capacitance between Terminals at $V_R = 1$ V, $f = 1$ MHz	C_T	-	2	-	pF



Dated : 04/12/2007

